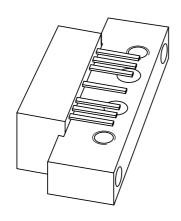
DISCRETE SEMICONDUCTORS

DATA SHEET



BGE788 750 MHz, 34 dB gain push-pull amplifier

Product specification Supersedes data of 1998 Jan 08

2001 Nov 15





750 MHz, 34 dB gain push-pull amplifier

BGE788

FEATURES

- · Excellent linearity
- · Extremely low noise
- High gain
- · Excellent return loss properties.

APPLICATIONS

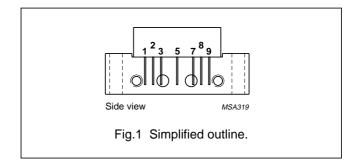
• Single module line extender in CATV systems operating in the 40 to 750 MHz frequency range.

DESCRIPTION

Hybrid high dynamic range amplifier module operating at a supply voltage of 24 V (DC) in a SOT115J package. The module consists of two cascaded stages both in cascode configuration.

PINNING - SOT115J

PIN	DESCRIPTION	
1	input	
2	common	
3	common	
5	+V _B	
7	common	
8	common	
9	output	



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Gp	power gain	f = 50 MHz	33.5	34.5	dB
		f = 750 MHz	34	_	dB
I _{tot}	total current consumption (DC)	V _B = 24 V	290	320	mA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER		MAX.	UNIT
V _B	supply voltage		25	٧
Vi	RF input voltage		55	dBmV
T _{stg}	storage temperature		+100	°C
T _{mb}	mounting base operating temperature		+100	°C

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CHARACTERISTICS

Bandwidth 40 to 750 MHz; V_B = 24 V; T_{case} = 30 °C; Z_S = Z_L = 75 Ω .

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Gp	power gain	f = 50 MHz	33.5	34.5	dB
·		f = 750 MHz	34	_	dB
SL	slope cable equivalent	f = 40 to 750 MHz	0.5	2.5	dB
FL	flatness of frequency response	f = 40 to 750 MHz	_	±0.5	dB
s ₁₁	input return losses	f = 40 to 80 MHz	20	_	dB
		f = 80 to 160 MHz	18.5	_	dB
		f = 160 to 320 MHz	17	_	dB
		f = 320 to 640 MHz	15.5	_	dB
		f = 640 to 750 MHz	14	_	dB
S ₂₂	output return losses	f = 40 to 80 MHz	20	_	dB
		f = 80 to 160 MHz	18.5	_	dB
		f = 160 to 320 MHz	17	_	dB
		f = 320 to 640 MHz	15.5	_	dB
		f = 640 to 750 MHz	14	_	dB
s ₂₁	phase response	f = 50 MHz	135	225	deg
СТВ	composite triple beat	110 channels flat; V _o = 44 dBmV; measured at 745.25 MHz	_	-49	dB
X _{mod}	cross modulation	110 channels flat; V _o = 44 dBmV; measured at 55.25 MHz	-	-51	dB
CSO	composite second order distortion	110 channels flat; V _o = 44 dBmV; measured at 746.5 MHz	-	-52	dB
d ₂	second order distortion	note 1	_	-64	dB
Vo	output voltage	$d_{im} = -60 \text{ dB}$; note 2	58	_	dBmV
F	noise figure	f = 750 MHz	_	7	dB
PM	positive match	f = 40 MHz to 2 GHz	_	3	dB
I _{tot}	total current consumption (DC)	note 3	290	320	mA

Notes

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1. f_p = 55.25 MHz; V_p = 44 dBmV; f_q = 691.25 MHz; V_q = 44 dBmV; measured at f_p + f_q = 746.5 MHz.
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2. Measured according to DIN45004B;

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\begin{split} f_p &= 740.25 \text{ MHz; } V_p = V_o; \\ f_q &= 747.25 \text{ MHz; } V_q = V_o - 6 \text{ dB;} \\ f_r &= 749.25 \text{ MHz; } V_r = V_o - 6 \text{ dB;} \\ \text{measured at } f_p + f_q - f_r = 738.25 \text{ MHz.} \end{split}
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3. The module normally operates at V_B = 24 V, but is able to withstand supply transients up to 30 V.

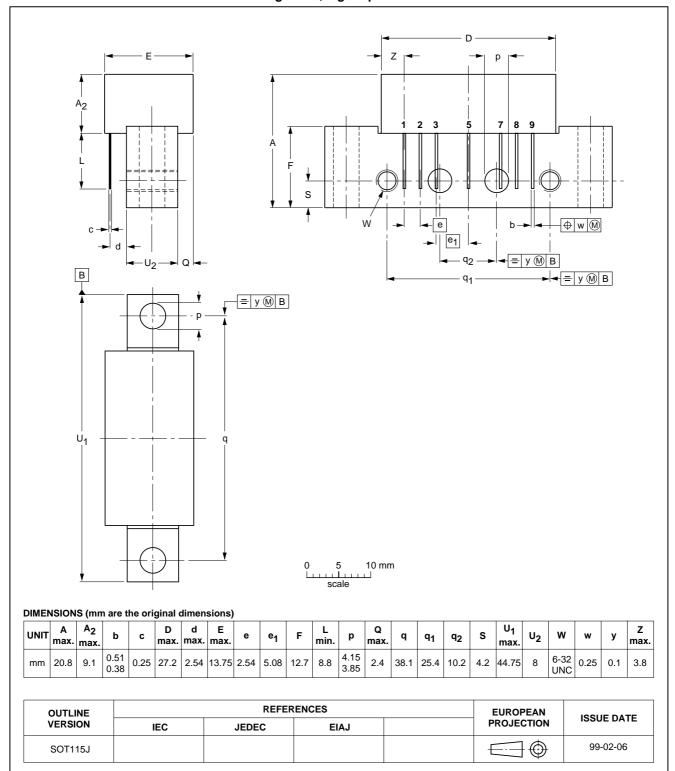
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PACKAGE OUTLINE

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J



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DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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NOTES

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NOTES

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Printed in The Netherlands

613518/03/pp8

Date of release: 2001 Nov 15

Document order number: 9397 750 08812

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